



**DONGGUAN NANJING ELECTRONICS LTD.,**  
**SOT-23 Plastic-Encapsulate Transistors**

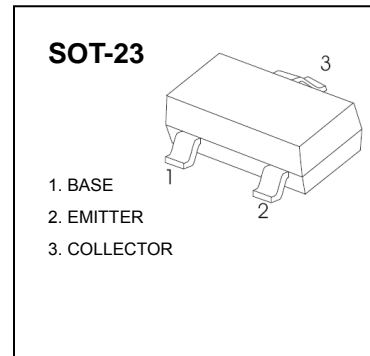
**S9015** TRANSISTOR (PNP)

**FEATURES**

- Complementary to S9014

**MARKING: M6**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**



Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.1	A
P <sub>C</sub>	Collector Power Dissipation	0.2	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0	-50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -0.1mA, I <sub>B</sub> = 0	-45			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> = 0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -50 V, I <sub>E</sub> = 0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1mA	200		1000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f = 30MHz	150			MHz

**CLASSIFICATION OF h<sub>FE</sub>**

Rank	L	H
Range	200-450	450-1000

# Typical Characteristics

# S9015

